

RM600DG-130S

HIGH POWER SWITCHING USE
INSULATED TYPE

High Voltage Diode Module

RM600DG-130S



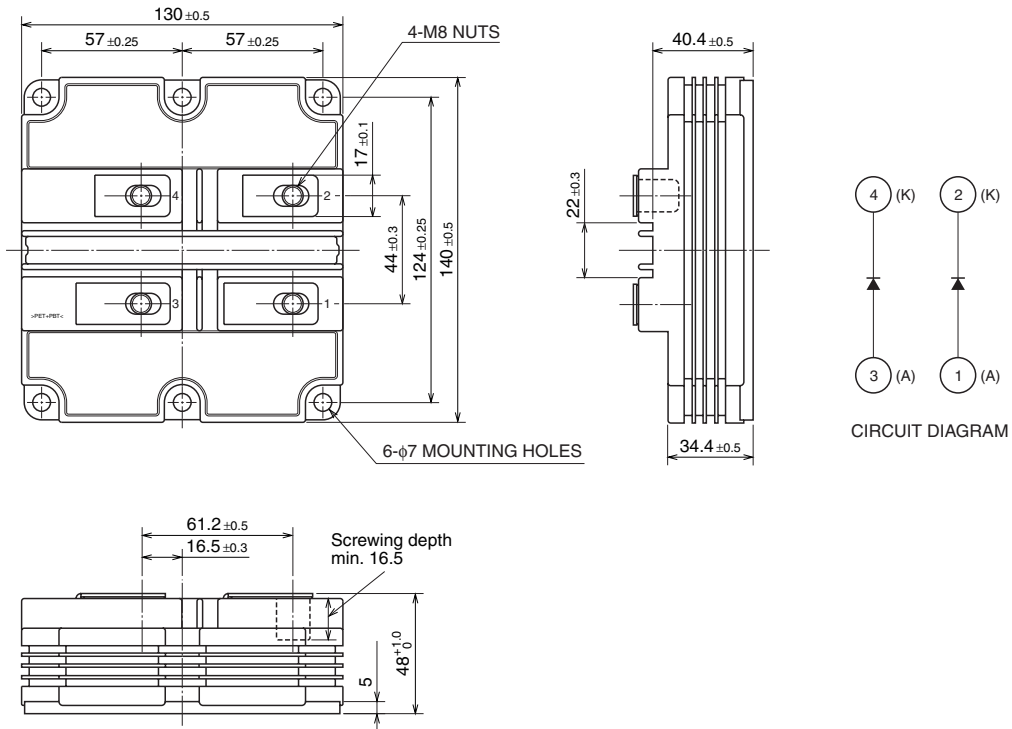
- IF 600A
- VRRM 6500V
- High Insulated Type
- 2-element in a Pack
- AISiC Baseplate

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS

| Symbol | Item | Conditions | Ratings | Unit |
|------------------|--------------------------------------|---|------------|-------------------|
| VRRM | Repetitive peak reverse voltage | T _j = -40 °C | 5800 | V |
| | | T _j = +25 °C | 6300 | |
| | | T _j = +125 °C | 6500 | |
| VRSM | Non-repetitive peak reverse voltage | T _j = -40 °C | 5800 | V |
| | | T _j = +25 °C | 6300 | |
| | | T _j = +125 °C | 6500 | |
| VR(DC) | Reverse DC voltage | T _j = 25 °C | 4500 | V |
| IF | DC forward current | Tc = 25 °C | 600 | A |
| IFSM | Surge forward current | T _j = 25 °C start, tw = 8.3 ms Half sign wave | 4800 | A |
| i ² t | Current-squared, time integration | T _j = 25 °C start, tw = 8.3 ms Half sign wave | 96 | kA ² s |
| V _{iso} | Isolation voltage | Charged part to the baseplate RMS sinusoidal, 60Hz 1min. | 10200 | V |
| V _e | Partial discharge extinction voltage | RMS sinusoidal, 60Hz, QPD ≤ 10PC | 5100 | V |
| T _j | Junction temperature | — | -40 ~ +150 | °C |
| T _{op} | Operating temperature | — | -40 ~ +125 | °C |
| T _{stg} | Storage temperature | — | -40 ~ +125 | °C |

ELECTRICAL CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|------------------|----------------------------------|---|-------------------------|------|------|------|
| | | | Min | Typ | Max | |
| IRRM | Repetitive reverse current | V _{RM} = VRRM | T _j = 25 °C | — | 10 | mA |
| | | | T _j = 125 °C | — | 90 | |
| VFM | Forward voltage (Note 1) | IF = 600 A | T _j = 25 °C | — | 4.00 | V |
| | | | T _j = 125 °C | — | 3.60 | |
| t _{rr} | Reverse recovery time | V _R = 3600 V, IF = 600 A di/dt = -2000 A/μs L _s =100nH, T _j = 125 °C | — | 1.0 | — | μs |
| I _{rr} | Reverse recovery current | | — | 1250 | — | A |
| Q _{rr} | Reverse recovery charge | | — | 900 | — | μC |
| E _{rec} | Reverse recovery energy (Note 2) | | — | 2.0 | — | J/P |

Note 1. It doesn't include the voltage drop by internal lead resistance.
 2. E_{rec} is the integral of 0.1V_R x 0.1I_{rr} x dt.

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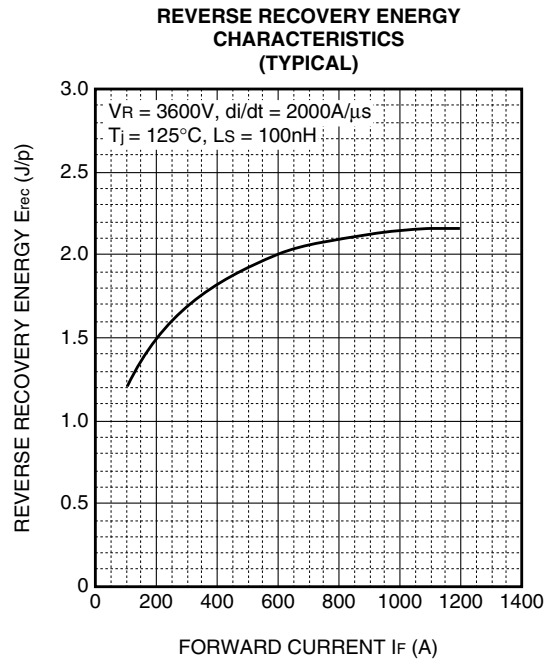
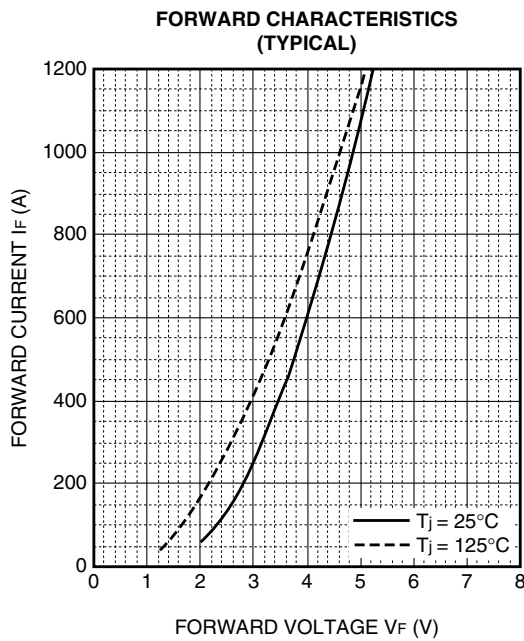
THERMAL CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|---------------|----------------------------|---|--------|------|------|------|
| | | | Min | Typ | Max | |
| $R_{th(j-c)}$ | Thermal resistance | Junction to case (per 1/2 module) | — | — | 22.0 | K/kW |
| $R_{th(c-f)}$ | Contact thermal resistance | Case to Fin, $\lambda_{grease} = 1W/m \cdot K$ $D_{(c-f)} = 100\mu m$, (per 1/2 module) | — | 16.0 | — | K/kW |

MECHANICAL CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|-------------|----------------------------|--------------------------|--------|------|------|------------|
| | | | Min | Typ | Max | |
| M_t | Mounting torque | M8: Main terminals screw | 7.0 | — | 15.0 | N·m |
| M_s | | M6: Mounting screw | 3.0 | — | 6.0 | N·m |
| m | Mass | — | — | 1.0 | — | kg |
| CTI | Comparative tracking index | — | 600 | — | — | — |
| D_a | Clearance | — | 26 | — | — | mm |
| D_s | Creepage distance | — | 56 | — | — | mm |
| LP CE | Internal inductance | — | — | 44 | — | nH |
| R_{CC+EE} | Internal lead resistance | $T_c = 25^\circ C$ | — | 0.27 | — | m Ω |

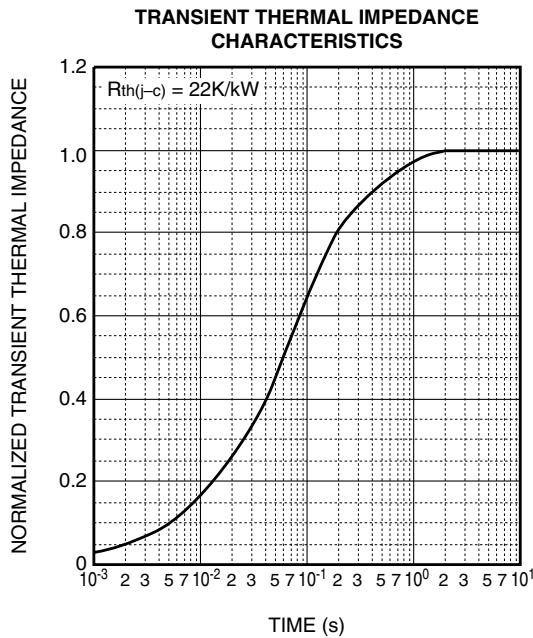
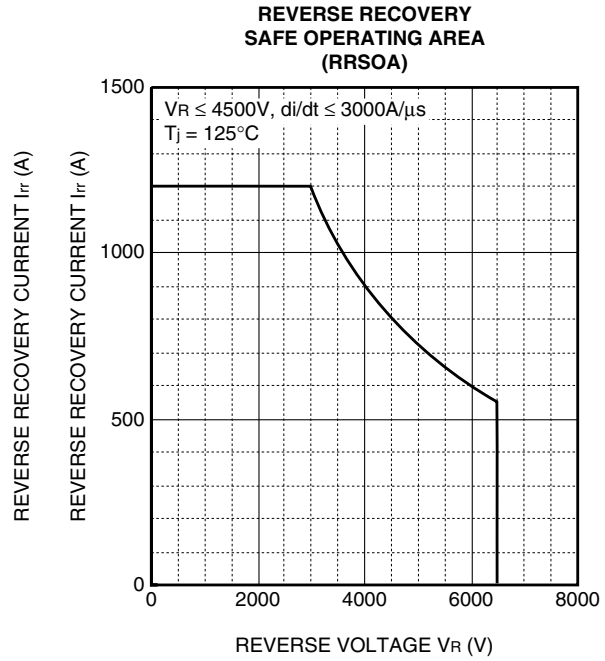
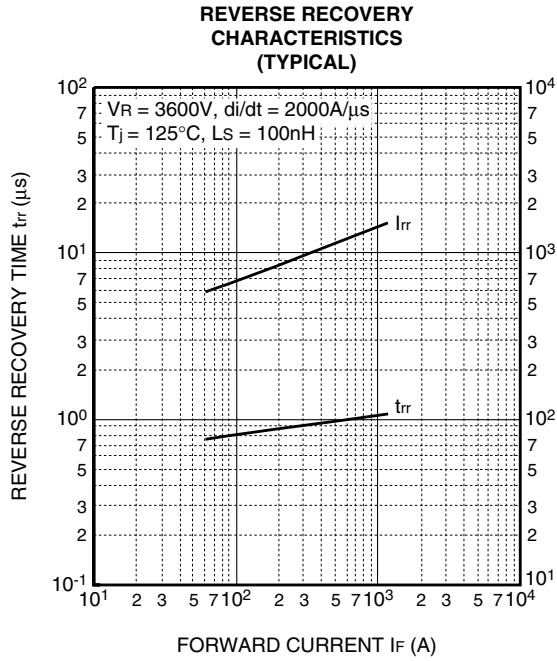
PERFORMANCE CURVES



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$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

| | 1 | 2 | 3 | 4 |
|----------------|--------|--------|--------|--------|
| R_i [K/kW] | 0.0059 | 0.0978 | 0.6571 | 0.2392 |
| τ_i [sec] | 0.0002 | 0.0074 | 0.0732 | 0.4488 |

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